

Amendments to the Claims:

Please amend claims 1-4, 8-11 and 15-18 as shown in the following listing of claims. This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (currently amended) A device for emitting output light, said device comprising:
a semiconductor chip that emits first light of a first peak wavelength in a 481-520 nm range; and
a wavelength-shifting region optically coupled to said semiconductor chip to receive said first light, said wavelength-shifting region including Group IIB element Selenide-based phosphor material having a property to convert some of said first light to second light of a second peak wavelength in a red wavelength range, said Group IIB element Selenide-based phosphor material including Group IIB element Selenide exclusively activated by ~~at least one~~ an element selected from a group consisting of Copper, Chlorine, Fluorine, Bromine and Silver, said first light and said second light being components of said output light.

2. (currently amended) The device of claim 1 wherein said Group IIB element ~~Selenide is Selenide-based phosphor material of said wavelength-shifting region~~ includes Zinc Selenide.

3. (currently amended) The device of claim 2 wherein said Group IIB element Selenide-based phosphor material of said wavelength-shifting region includes said Zinc Selenide exclusively activated by Copper.

4. (currently amended) The device of claim 1 wherein said Group IIB element ~~Selenide is Selenide-based phosphor material of said wavelength-shifting region~~ includes Cadmium Selenide.

1 5. (previously presented) The device of claim 1 wherein said semiconductor chip
2 is a light emitting diode die that can generate said first light of said first peak
3 wavelength.

1 6. (previously presented) The device of claim 1 wherein said wavelength-shifting
2 region is a part of a lamp coupled to said semiconductor chip.

1 7. (previously presented) The device of claim 1 wherein said wavelength-shifting
2 region is a lamp coupled to said semiconductor chip.

1 8. (currently amended) A device for emitting output light, said device
2 comprising:
3 a semiconductor die that emits first light of a first peak wavelength in a
4 481-520 nm range; and
5 a phosphor-containing medium positioned to receive said first light,
6 said phosphor-containing medium including Group IIB element Selenide-based
7 phosphor material having a property to convert some of said first light to second light
8 of a second peak wavelength in a red wavelength range, said Group IIB element
9 Selenide-based phosphor material including Group IIB element Selenide exclusively
10 activated by ~~at least one~~ an element selected from a group consisting of Copper,
11 Chlorine, Fluorine, Bromine and Silver, said first light and said second light being
12 components of said output light.

1 9. (currently amended) The device of claim 8 wherein said Group IIB element
2 Selenide is Selenide-based phosphor material of said phosphor-containing medium
3 includes Zinc Selenide.

1 10. (currently amended) The device of claim 9 wherein said Group IIB element
2 Selenide-based phosphor material of said phosphor-containing medium includes said
3 Zinc Selenide exclusively activated by Copper.

1 11. (currently amended) The device of claim 8 wherein said Group IIB element
2 Selenide is Selenide-based phosphor material of said phosphor-containing medium
3 includes Cadmium Selenide.

1 12. (original) The device of claim 8 wherein said semiconductor die is a light
2 emitting diode die.

1 13. (previously presented) The device of claim 8 wherein said phosphor-
2 containing medium is a part of a lamp coupled to said semiconductor die.

1 14. (previously presented) The device of claim 8 wherein said phosphor-
2 containing medium is a lamp coupled to said semiconductor die.

1 15. (currently amended) A method for emitting output light, said method
2 comprising:
3 generating first light of a first peak wavelength in a 481-520 nm range
4 at a semiconductor die, including emitting said first light out of said semiconductor
5 die;
6 receiving said first light emitted out of said semiconductor die,
7 including converting some of said first light to second light of a second peak
8 wavelength in a red wavelength range using Group IIB element Selenide-based
9 phosphor material, said Group IIB element Selenide-based phosphor material
10 including Group IIB element Selenide exclusively activated by ~~at least one~~ an element
11 selected from a group consisting of Copper, Chlorine, Fluorine, Bromine and Silver;
12 and
13 emitting said first light and said second light as components of said
14 output light.

1 16. (currently amended) The method of claim 15 wherein said Group IIB element
2 Selenide is Selenide-based phosphor material includes Zinc Selenide.

1 17. (currently amended) The method of claim 16 wherein said Group IIB element
2 Selenide-based phosphor material includes said Zinc Selenide exclusively activated
3 by Copper.

1 18. (currently amended) The method of claim 15 wherein said Group IIB element
2 Selenide is Selenide-based phosphor material includes Cadmium Selenide.

1 19. (original) The method of claim 15 wherein said generating includes generating
2 said first light of said first peak wavelength at a light emitting diode die.

1 20. (original) The method of claim 19 wherein said light emitting diode die is
2 configured to generate said first light such that said first peak wavelength is within a
3 blue-green region of the visible light spectrum.